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Fig. 1

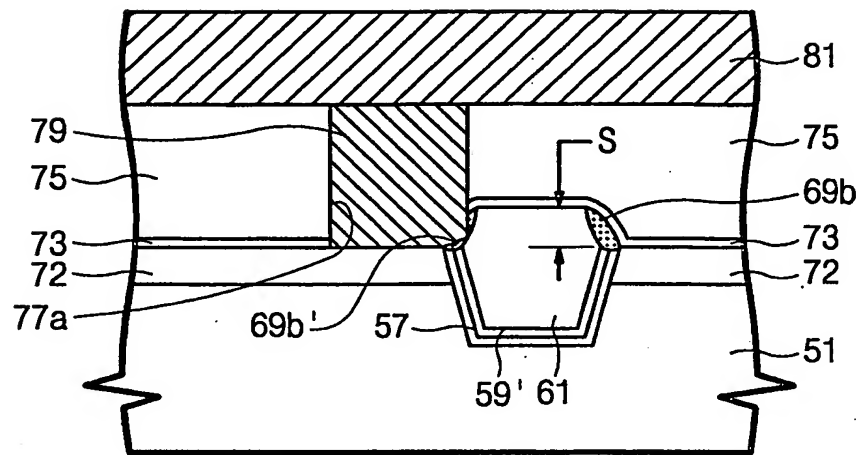


Fig. 2

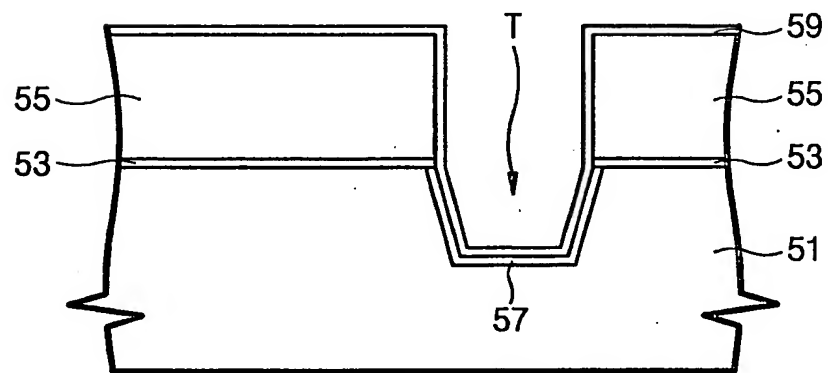


Fig. 3

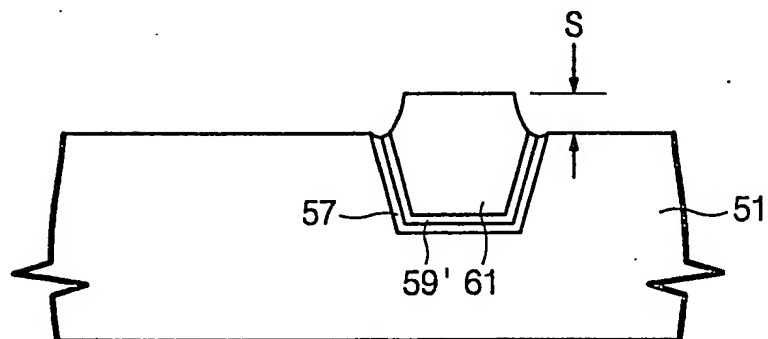


Fig. 4

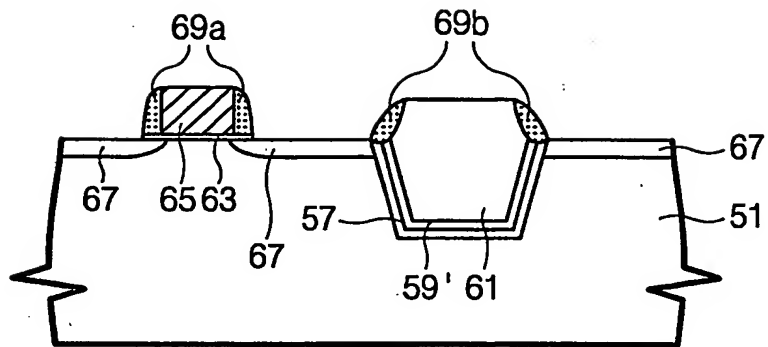
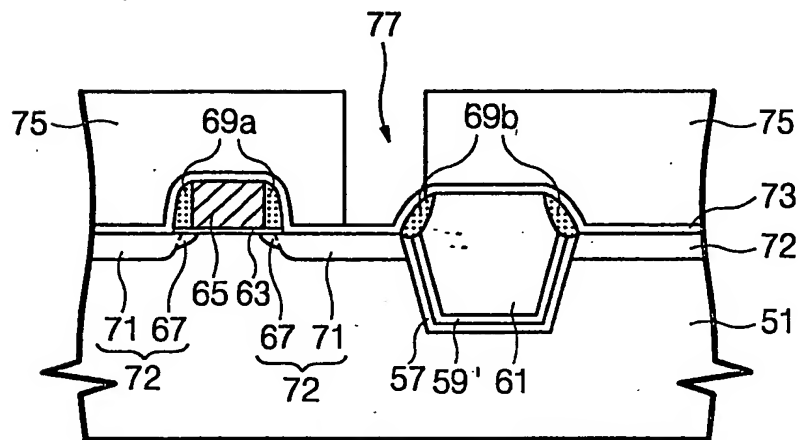


Fig. 5



This cross-sectional view shows a semiconductor device with a central gate structure and two side gates. The central gate structure includes a gate stack 79 on a gate dielectric 75, with a gate electrode 61 and a gate contact 59' at the bottom. The side gates consist of a gate stack 73 on a gate dielectric 75, with a gate electrode 63 and a gate contact 57 at the bottom. The device is formed on a substrate 51. The central gate structure is flanked by two side gates, and the entire device is surrounded by a protective layer 72. The central gate structure is labeled 69a and the side gates are labeled 69b. The gate dielectric is labeled 75, the gate electrode is labeled 61, the gate contact is labeled 59', the side gate dielectric is labeled 73, the side gate electrode is labeled 63, and the side gate contact is labeled 57. The protective layer is labeled 72. The substrate is labeled 51. The central gate structure is flanked by two side gates, and the entire device is surrounded by a protective layer 72.

Fig. 8a

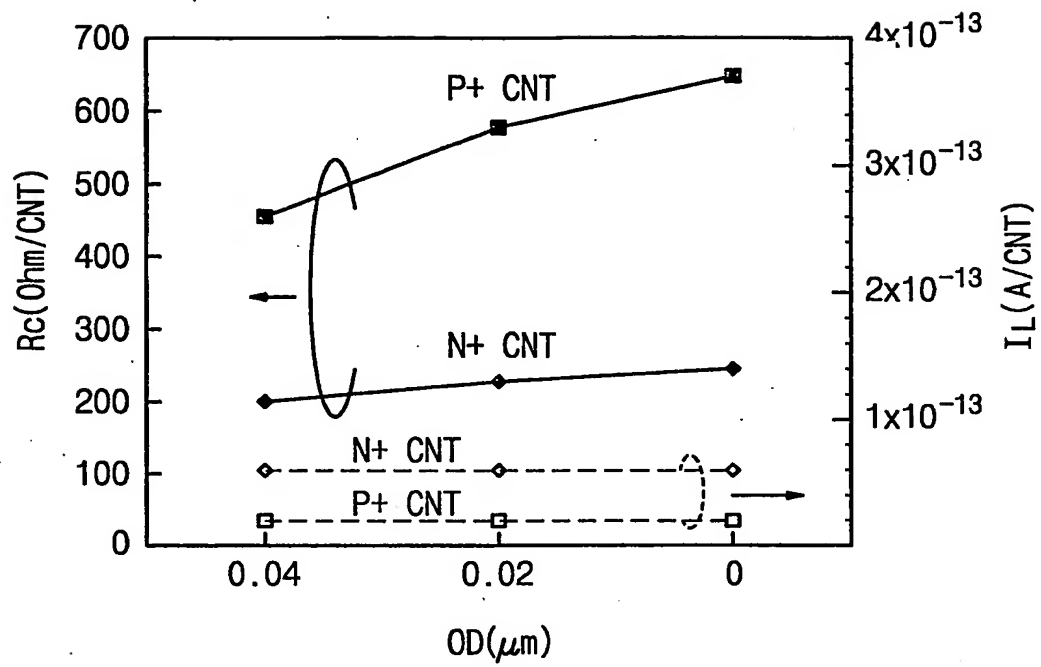


Fig. 8b

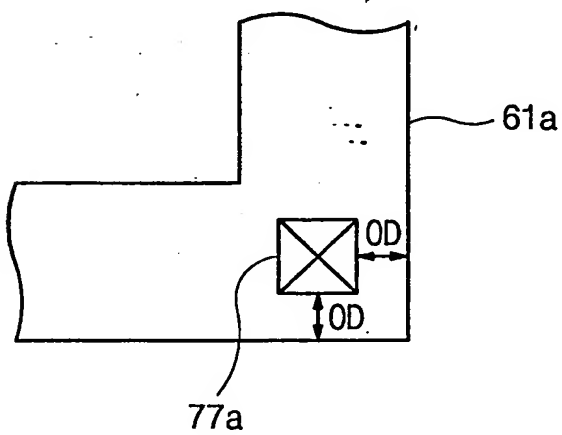


Fig. 9

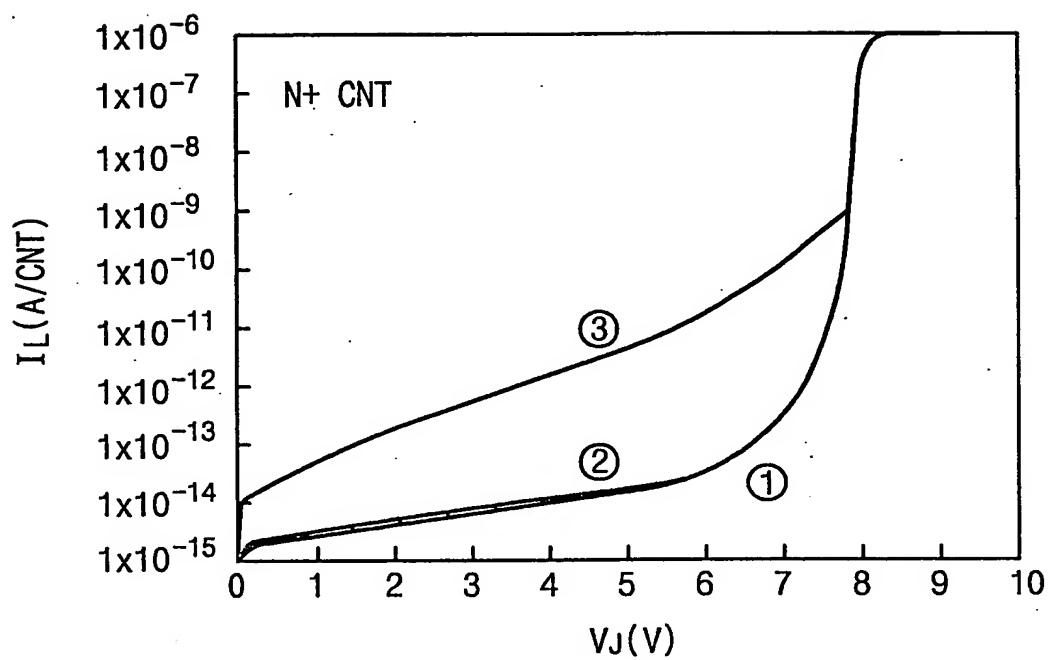


Fig. 10

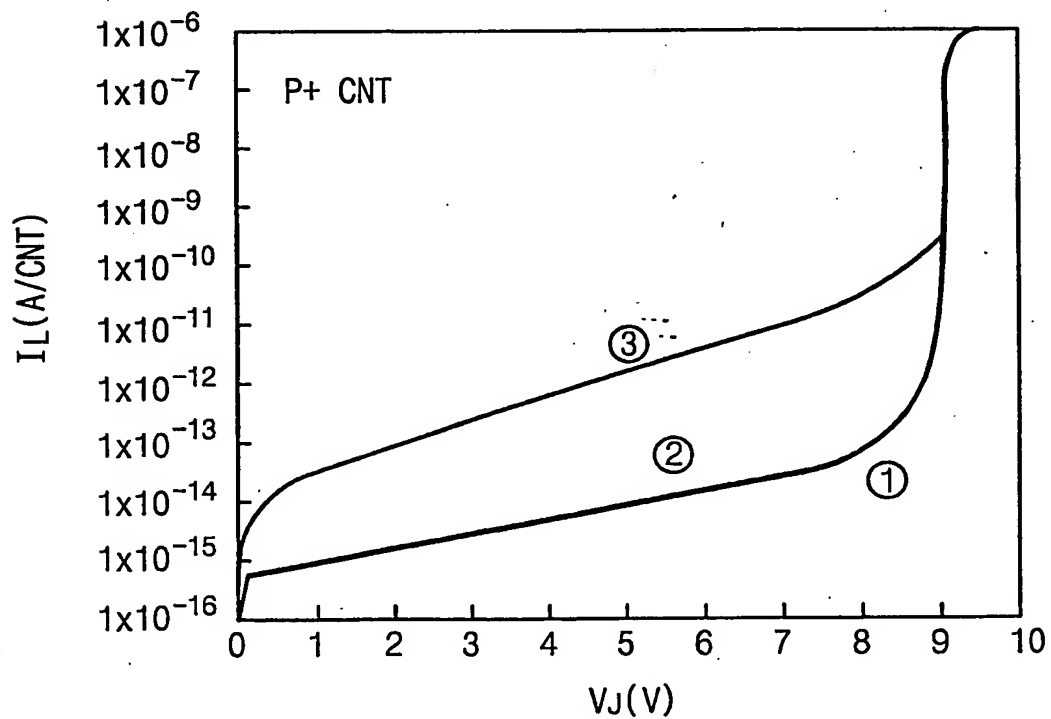


Fig. 11

